

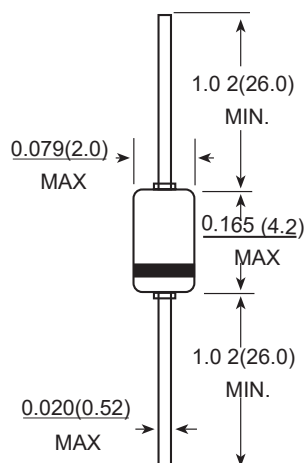
DO-35 Small Signal Switching Diodes

FEATURES

- Fast Switching Speed
- Electrically Identical to Standard JEDEC
- High reliability
- Lead free in compliance with EU RoHS 2.0
- Component in accordance to RoHS 2015/863 and WEEE 2012/19/EU

MECHANICAL DATA

- Case style: DO-35, glass case
- Mounting position: Any



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Power Dissipation	P_d	500	mW
Operating junction temperature	T_j	175	°C
Storage temperature range	T_s	-65-+200	°C
Working Inverse Voltage	W_{IV}	75	V
Average Rectified Current	I_o	150	mA
Non-repetitive Peak Forward Current	I_{FM}	450	mA

@ $t < 1s$ and $T_j = 25^\circ C$

Symbols	Parameter	Test Condition	Limits		Unit
			Min	Max	
BV	Breakdown Voltage	$I_R = 100\mu A$	100		V
		$I_R = 5\mu A$	75		
IR	Reverse Leakage Current	$V_R = 20V$	---	25	nA
		$V_R = 75$	---	5	uA
VF	Forward Voltage	1N4448/1N914B $I_F = 5mA$	0.62	0.72	V
		1N4148 $I_F = 10mA$	---	1	
		1N4448/1N914B $I_F = 100mA$	---	1	
TRR	Reverse Recovery Time	$I_F = 10mA, I_R = 1.0mA$ $R_L = 100\Omega$ $I_{RR} = 1mA$	---	4	nS
C	Capacitance	$V_R = 0V, f = 1MHz$	---	4	pF

RATINGS AND CHARACTERISTIC CURVES

FIG.1 -- ADMISSIBLE POWER DISSIPATION
VERSUS AMBIENT TEMPERATURE

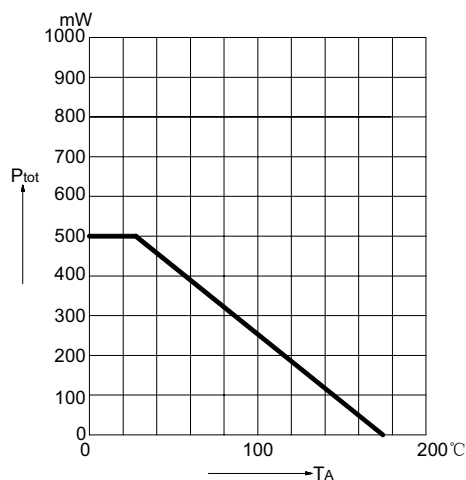


FIG.2 – FORWARD CHARACTERISTICS

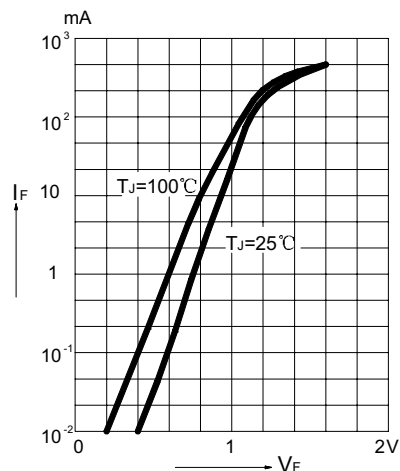


FIG.3 – ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

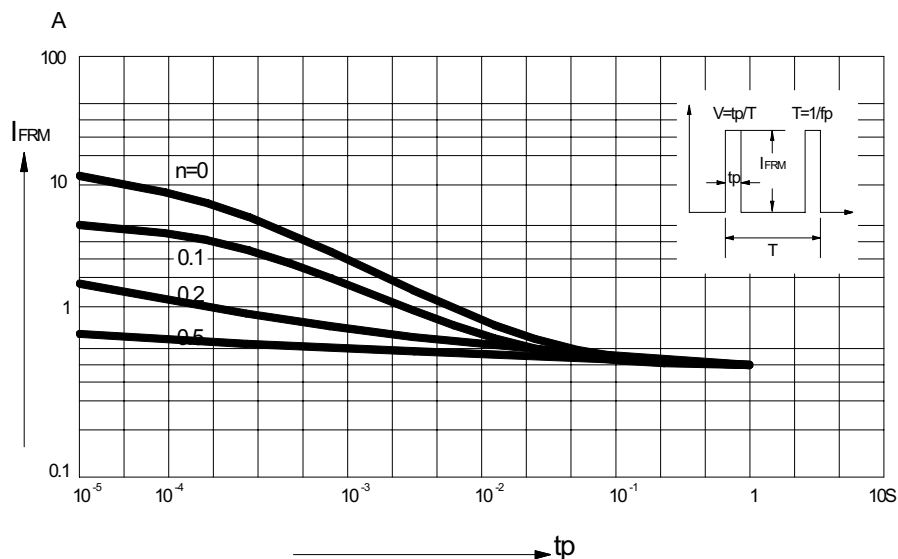


FIG.4 – RECTIFICATION EFFICIENCY
MEASUREMENT CIRCUIT

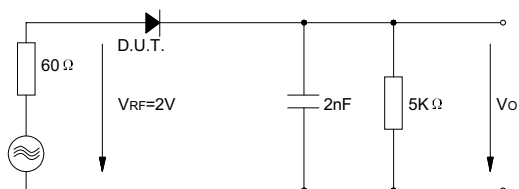


FIG.5 – RELATIVE CAPACITANCE VERSUS
VOLTAGE

